

PSMN016-100BS

N-channel 100V 16 m Ω standard level MOSFET in D2PAK Rev. 2 — 1 March 2012 Product data

Product data sheet

Product profile 1.

1.1 General description

Standard level N-channel MOSFET in a D2PAK packages qualified to 175C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

1.2 Features and benefits

- High efficiency due to low switching and conduction losses
- Suitable for standard level gate drive

1.3 Applications

- DC-to-DC converters
- Load switching

- Motor control
- Server power supplies

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Cyllibol	i didilictoi		141111	ijΡ	WIGA	Oint
V_{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	-	100	V
I _D	drain current	$T_j = 25 \text{ °C}; V_{GS} = 10 \text{ V}; \text{ see } \frac{\text{Figure 1}}{}$	-	-	57	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	-	148	W
Tj	junction temperature		-55	-	175	°C
Static chara	Static characteristics					
R _{DSon}	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A}; T_j = 100 °C; \text{see}$ <u>Figure 12</u>	-	-	28.8	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A}; T_j = 25 ^{\circ}\text{C};$ see Figure 13	-	13	16	mΩ
Dynamic cha	aracteristics					
Q_{GD}	gate-drain charge	$V_{GS} = 10 \text{ V}; I_D = 30 \text{ A}; V_{DS} = 50 \text{ V};$	-	15	-	nC
Q _{G(tot)}	total gate charge	see <u>Figure 14</u> ; see <u>Figure 15</u>	-	49	-	nC
Avalanche ruggedness						
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 60 A; V_{sup} ≤ 100 V; unclamped; R_{GS} = 50 Ω	-	-	101	mJ



2. Pinning information

Table 2. Pinning information

		•		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		_
2	D	drain[1]	mb	D
3	S	source		
	S	source	/\	
mb	D	mounting base; connected to drain	1 3	mbb076 S
			SOT404 (D2PAK)	

^[1] It is not possible to make connection to pin 2

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PSMN016-100BS	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage	$T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}$	-	100	V
V_{DGR}	drain-gate voltage	$T_j \le 175 \text{ °C}; T_j \ge 25 \text{ °C}; R_{GS} = 20 \text{ k}\Omega$	-	100	V
V_{GS}	gate-source voltage		-20	20	V
I _D	drain current	$V_{GS} = 10 \text{ V}; T_{mb} = 100 ^{\circ}\text{C}; \text{ see } \frac{\text{Figure 1}}{\text{Model}}$	-	40	Α
		$V_{GS} = 10 \text{ V}; T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 1}}{}$	-	57	Α
I _{DM}	peak drain current	pulsed; $t_p \le 10 \mu s$; $T_{mb} = 25 \text{ °C}$; see Figure 3	-	230	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	148	W
T _{stg}	storage temperature		-55	175	°C
T _j	junction temperature		-55	175	°C
T _{sld(M)}	peak soldering temperature		-	260	°C
Source-drai	in diode				
I _S	source current	T _{mb} = 25 °C	-	57	Α
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$	-	230	Α
Avalanche i	ruggedness				
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 60 A; V_{sup} ≤ 100 V; unclamped; R_{GS} = 50 Ω	-	101	mJ

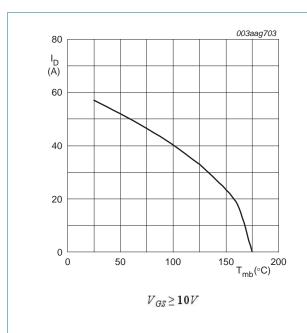


Fig 1. Continuous drain current as a function of mounting base temperature

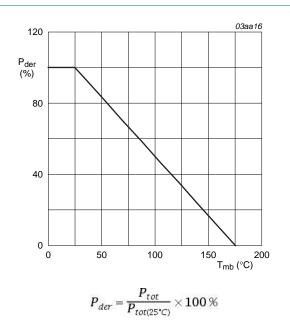
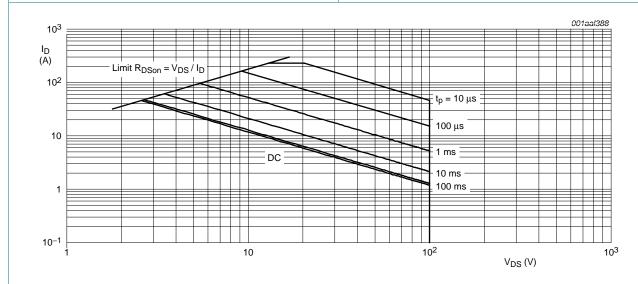


Fig 2. Normalized total power dissipation as a function of mounting base temperature



 $T_{mb} = 25$ °C; I_{DM} is a single pulse

Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 4	-	0.56	1.01	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient		<u>[1]</u> _	50	-	K/W

[1] minimum footprint; mounted on a printed-circuit board to ambient

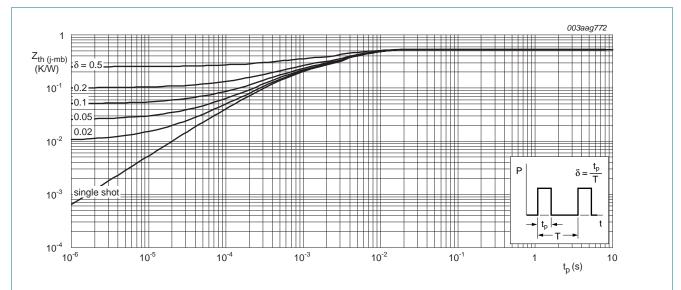


Fig 4. Transient thermal impedance from junction to mounting base as a function of pulse duration; typical values

6. Characteristics

Table 6 Characteristics

Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
V _{(BR)DSS}	drain-source breakdown	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = -55 \text{ °C}$	90	-	-	V
	voltage	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	100	-	-	V
V _{GS(th)} 9	gate-source threshold voltage	$I_D = 1$ mA; $V_{DS} = V_{GS}$; $T_j = 175$ °C; see Figure 10	1	-	-	V
		$I_D = 1$ mA; $V_{DS} = V_{GS}$; $T_j = 25$ °C; see <u>Figure 11</u> ; see <u>Figure 10</u>	2	3	4	V
		$I_D = 1$ mA; $V_{DS} = V_{GS}$; $T_j = -55$ °C; see Figure 10	-	-	4.8	V
I _{DSS} drain	drain leakage current	$V_{DS} = 100 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 125 \text{ °C}$	-	-	100	μΑ
		$V_{DS} = 100 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.05	5	μΑ
I _{GSS} gate leakage current	gate leakage current	$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	10	100	nA
		$V_{GS} = -20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	10	100	nA
R _{DSon} drain-source on-state resistance		$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A}; T_j = 100 ^{\circ}\text{C};$ see Figure 12	-	-	28.8	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A}; T_j = 175 ^{\circ}\text{C};$ see Figure 12	-	36.4	44.8	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A}; T_j = 25 \text{ °C};$ see Figure 13	-	13	16	mΩ
R_G	internal gate resistance (AC)	f = 1 MHz	-	0.9	-	Ω
Dynamic	characteristics					
$Q_{G(tot)}$	total gate charge	$I_D = 0$ A; $V_{DS} = 0$ V; $V_{GS} = 10$ V; see Figure 14	-	40	-	nC
		$I_D = 30 \text{ A}; V_{DS} = 50 \text{ V}; V_{GS} = 10 \text{ V};$	-	49	-	nC
Q_{GS}	gate-source charge	see <u>Figure 14</u> ;see <u>Figure 15</u>	-	12	-	nC
Q _{GS(th)}	pre-threshold gate-source charge	$I_D = 30 \text{ A}; V_{DS} = 50 \text{ V}; V_{GS} = 10 \text{ V};$ see Figure 14	-	7.75	-	nC
Q _{GS(th-pl)}	post-threshold gate-source charge		-	4.25	-	nC
Q_GD	gate-drain charge	$I_D = 30 \text{ A}$; $V_{DS} = 50 \text{ V}$; $V_{GS} = 10 \text{ V}$; see Figure 14;see Figure 15	-	15	-	nC
$V_{GS(pl)}$	gate-source plateau voltage	V _{DS} = 50 V; see <u>Figure 14</u> ; see <u>Figure 15</u>	-	4.5	-	V
C _{iss}	input capacitance	$V_{DS} = 50 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$	-	2404	-	pF
Coss	output capacitance	T _j = 25 °C; see <u>Figure 16</u>	-	189	-	pF
Crss	reverse transfer capacitance		-	113	-	pF
d(on)	turn-on delay time	$V_{DS} = 50 \text{ V}; R_L = 1.7 \Omega; V_{GS} = 10 \text{ V};$	-	17	-	ns
r	rise time	$R_{G(ext)} = 4.7 \Omega; T_j = 25 ^{\circ}C$	-	23	-	ns
t _{d(off)}	turn-off delay time		-	36	-	ns
t _f	fall time		-	18	-	ns

Table 6. Characteristics ... continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Source-drain diode						
V_{SD}	source-drain voltage	$I_S = 15 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C};$ see <u>Figure 17</u>	-	0.8	1.2	V
t _{rr}	reverse recovery time	$I_S = 10 \text{ A}$; $dI_S/dt = 100 \text{ A/}\mu\text{s}$; $V_{GS} = 0 \text{ V}$;	-	54	-	ns
Q _r	recovered charge	$V_{DS} = 50 \text{ V}$	-	126	-	nC

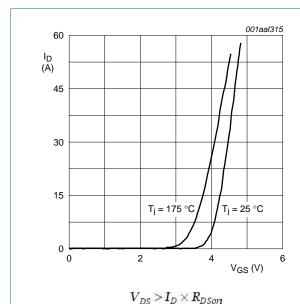


Fig 5. Transfer Characteristic: drain current as a function of gate-source voltage; typical values

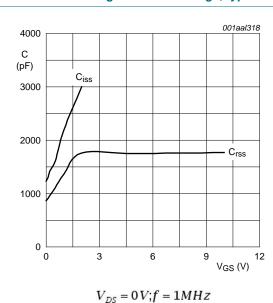
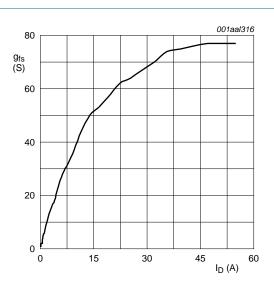
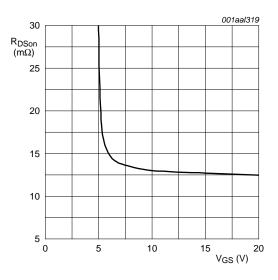


Fig 7. Input and revers transfer capacitances as a function of gate-source voltage; typical values



 $T_j = 25 \,{}^{\circ}C; V_{DS} = 10 \, V$

Fig 6. forward transconductance as a function of drain current; typical values



 $T_j=25\,^{\circ}C; I_D=5A$

Fig 8. Drain-source on-state resistance as a function of gate-source voltage; typical values

PSMN016-100BS

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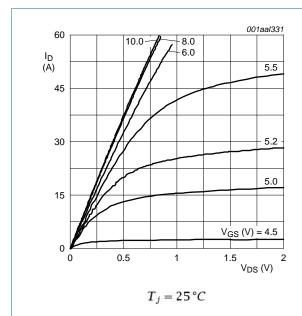


Fig 9. Output characteristics: drain current as a function of drain-source voltage; typical values

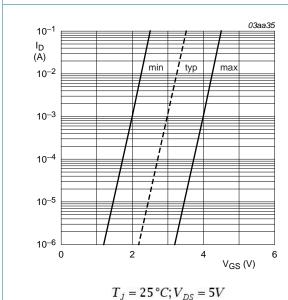


Fig 11. Sub-threshold drain current as a function of gate-source voltage

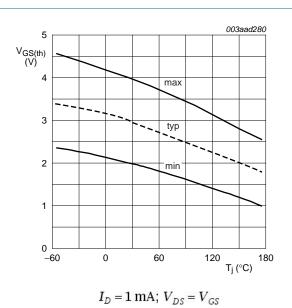


Fig 10. Gate-source threshold voltage as a function of junction temperature

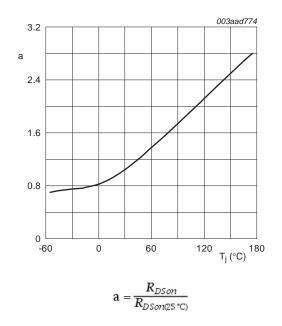
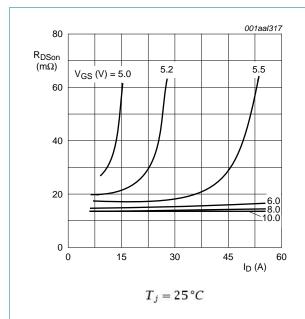


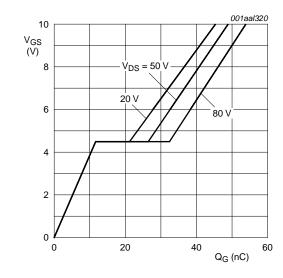
Fig 12. Normalized drain-source on-state resistance factor as a function of junction temperature

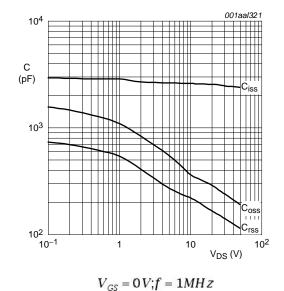


V_{GS}(pl)
V_{GS}(th)
V_{GS}
Q_{GS1} Q_{GS2}
Q_G(tot)
003aaa508

Fig 13. Drain-source on-state resistance as a function of drain current; typical values







 $T_j = 25 \,^{\circ}C; I_D = 30A$

Fig 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical

Fig 15. Gate-source voltage as a function of gate charge; typical values

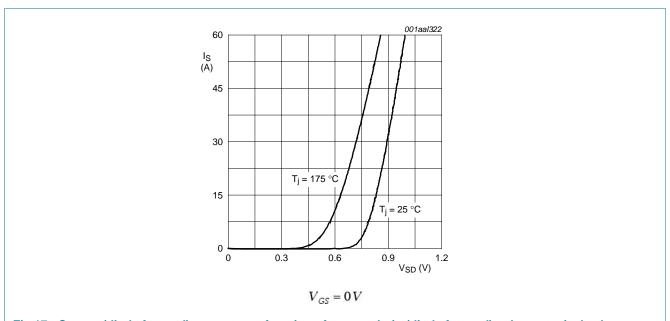


Fig 17. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

7. Package outline

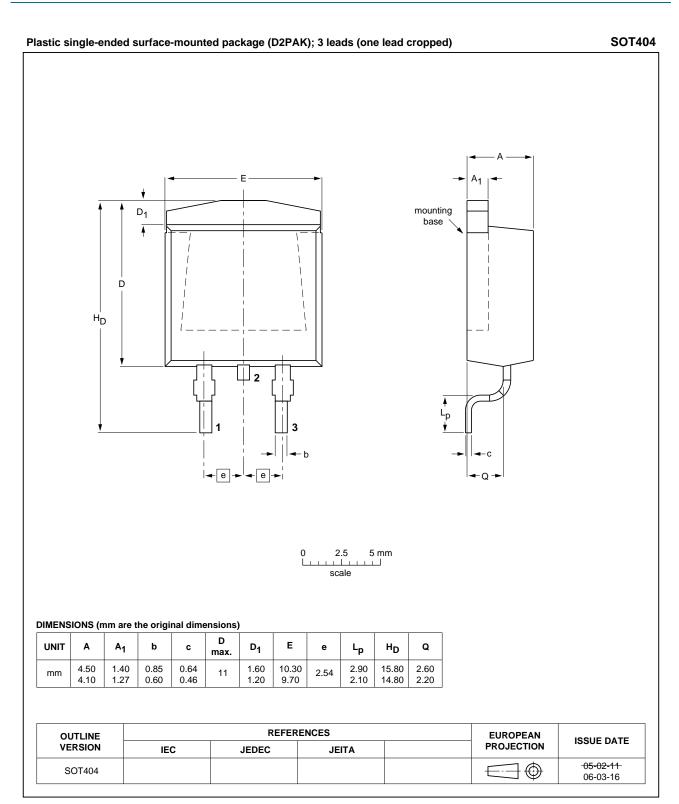


Fig 18. Package outline SOT404 (D2PAK)

Revision history

Table 7. **Revision history**

Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN016-100BS v.2	20120301	Product data sheet	-	PSMN016-100BS v.1
Modifications:	Status changed from the Various changes to the Various changes the Various changes to the Various changes to the Various changes to the Various changes the Various changes to the Various changes the Var	om objective to product. o content.		
PSMN016-100BS v.1	20111025	Objective data sheet	-	-

9. Legal information

9.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions'
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N-channel 100V 16 mΩ standard level MOSFET in D2PAK

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